Contribution ID: **10** Type: **not specified**

Effects of annealing on charge collection in heavily irradiated silicon micro-strip detectors

Tuesday 17 November 2009 11:45 (15 minutes)

Electric field and charge collection properties of a n+-p strip detector irradiated to 5e15 cm-2 were investigated by Edge-TCT (E-TCT) during long term annealing.
It was found that charge collection improves with time, due to larger avalanche multiplication. On the other hand, when operated under forward bias, charge collection properties of the detector were not affected by the annealing process.

Author: MILOVANOVIĆ, Marko (Jozef Stefan Institute, Ljubljana)

Co-authors: KRAMBERGER, Gregor (Jozef Stefan Institute, Ljubljana); MANDIĆ, Igor (Jozef Stefan Institute, Ljubljana); MIKUŽ, Marko (Jozef Stefan Institute, Ljubljana); ZAVRTANIK, Marko (Jozef Stefan Institute, Ljubljana); CINDRO, Vladimir (Jozef Stefan Institute, Ljubljana)

Presenter: MILOVANOVIĆ, Marko (Jozef Stefan Institute, Ljubljana)

Session Classification: Pad Detector Characterization & Studies on Charge Multiplication